

1N4150

FEATURES :

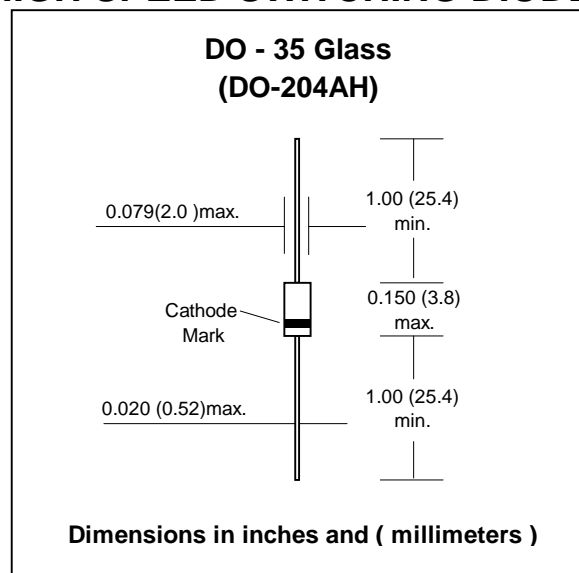
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 50 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 600 mA
- **Pb / RoHS Free**

MECHANICAL DATA :

Case: DO-35 Glass Case

Weight: approx. 0.13g

HIGH SPEED SWITCHING DIODE



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Maximum Continuous Reverse Voltage	V_{RM}	50	V
Maximum Continuous Forward Current	I_F	200	mA
Maximum Power Dissipation	P_D	500	mW
Maximum Repetitive Peak Forward Current	I_{FRM}	600	mA
Maximum Surge Forward Current at $t = 1s$, $T_j = 25^\circ C$	I_{FSM}	0.5	A
Maximum Junction Temperature	T_J	200	$^\circ C$
Storage Temperature Range	T_S	-65 to + 200	$^\circ C$

Electrical Characteristics ($T_J = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Current	I_R	$V_R = 50 V$	-	-	0.1	μA
		$V_R = 50 V$, $T_j = 150^\circ C$	-	-	100	μA
Forward Voltage	V_F	$I_F = 100 mA$	-	-	0.92	V
		$I_F = 200 mA$	-	-	1.0	V
Diode Capacitance	C_d	$f = 1MHz$; $V_R = 0$	-	-	2.5	pF
Reverse Recovery Time	T_{rr}	$I_F = 10 mA$ to 200 mA to $I_R = 10 mA$ to 200 mA; $R_L = 100 \Omega$; measured at $I_R = 0.1 \times I_F$	-	-	4	ns

RATING AND CHARACTERISTIC CURVES (1N4150)

FIG. 1 MAXIMUM FORWARD CURRENT VERSUS AMBIENT TEMPERATURE

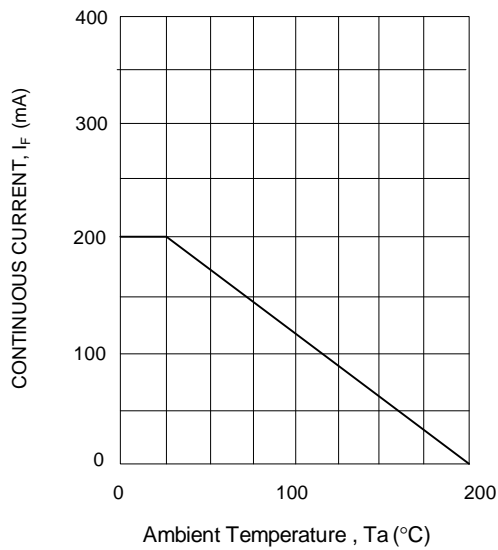


FIG. 2 TYPICAL FORWARD VOLTAGE

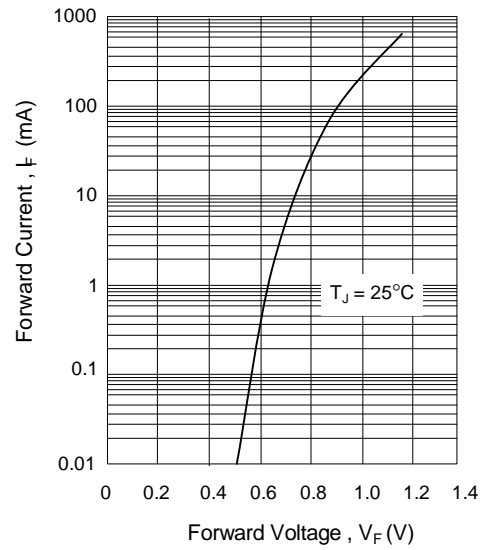


FIG. 3 TYPICAL DIODE CAPACITANCE AS A FUNCTION OF REVERSE VOLTAGE

